

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-24. (Canceled)

25. (Currently Amended) A complementary thin film transistor circuit, comprising:

a substrate;

a first thin film transistor that is formed on the substrate, the first thin film transistor including a first semiconductor film, a first gate electrode, and a first gate insulating film disposed between the first semiconductor film and the first gate electrode, the first semiconductor film including a first source region, a first drain region and a first channel region, the first thin film transistor being a first-conductivity-type thin film transistor; and

a second thin film transistor that is formed on the substrate, the second thin film transistor including a second semiconductor film, a second gate electrode, a second gate insulating film disposed between the second semiconductor film and the second gate electrode, the second semiconductor film including a second source region, a second drain region, and a second channel region, the second thin film transistor being a second-conductivity-type thin film transistor, the first drain region and the second drain region being in contact with each other, and the first source region and the second source region being in contact with each other, the first channel region and the second channel region being formed in a same crystal grain.

26. (Currently Amended) The complementary thin film transistor circuit according to claim 27~~claim 24~~, further comprising:

a plurality of crystal grains formed on the substrate, each of the plurality of crystal grains being a single crystal grain, one of the plurality of crystal grains including the first semiconductor film and the second semiconductor film.

27. A complementary thin film transistor circuit, comprising:

a substrate;

a first thin film transistor that is formed on the substrate, the first thin film transistor including a first semiconductor film, a first gate electrode, and a first gate insulating film disposed between the first semiconductor film and the first gate electrode, and the first semiconductor film including a first source region, a first drain region, and a first channel region;

a second thin film transistor that is formed on the substrate, the second thin film transistor including a second semiconductor film, a second gate electrode, a second gate insulating film disposed between the second semiconductor film and the second gate electrode, the second semiconductor film including a second source region, a second drain region and a second channel region, the first drain region and the second drain region being in contact with each other and the first source region being separated from the second source region, the first channel region and the second channel region being formed in a same crystal grain;

a first source electrode that is electrically contacting the first source region;

a second source electrode that is electrically contacting the second source region; and

a drain electrode that is electrically contacting the first drain region and the second drain region.

28. (Currently Amended) The complementary thin film transistor circuit according to claim 27~~claim 24~~, wherein the first channel region and the second channel region have a same plane orientation.

29. (Currently Amended) The complementary thin film transistor circuit according to claim 27~~claim 24~~, wherein the first thin film transistor is a first-conductivity-type thin film transistor and the second thin film transistor is a second-conductivity-type thin film transistor.

30. (Currently Amended) The complementary thin film transistor circuit according to claim 24, wherein A complementary thin film transistor circuit, comprising:
a substrate;
a first thin film transistor that is formed on the substrate, the first thin film transistor including a first semiconductor film, a first gate electrode, and a first gate insulating film disposed between the first semiconductor film and the first gate electrode, and the first semiconductor film including a first source region, a first drain region, and a first channel region,- the first thin film transistor has an electric field relief region between the first source region and the first channel region; and
a second thin film transistor that is formed on the substrate, the second thin film transistor including a second semiconductor film, a second gate electrode, a second gate insulating film disposed between the second semiconductor film and the second gate electrode, the second semiconductor film including a second source region, a second drain region and a second channel region, the first drain region and the second drain region being in contact with each other and the first source region being separated from the second source region, the first channel region and the second channel region being formed in a same crystal grain.

31. (Currently Amended) The complementary thin film transistor circuit according to claim 24, further comprising: A complementary thin film transistor circuit, comprising:

a substrate;

a first thin film transistor that is formed on the substrate, the first thin film transistor including a first semiconductor film, a first gate electrode, and a first gate insulating film disposed between the first semiconductor film and the first gate electrode, and the first semiconductor film including a first source region, a first drain region, and a first channel region;

a second thin film transistor that is formed on the substrate, the second thin film transistor including a second semiconductor film, a second gate electrode, a second gate insulating film disposed between the second semiconductor film and the second gate electrode, the second semiconductor film including a second source region, a second drain region and a second channel region, the first drain region and the second drain region being in contact with each other and the first source region being separated from the second source region, the first channel region and the second channel region being formed in a same crystal grain; and

an insulating film on the substrate, the first thin film transistor and the second thin film transistor being formed on the insulating film, the insulating film having a concave portion.

32. (Currently Amended) An electro-optical device, comprising:

the complementary thin film transistor circuit according to claim 27~~claim 24~~.